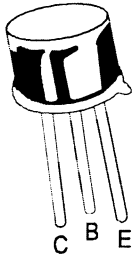




PNP SILICON PLANAR EPITAXIAL TRANSISTOR.

2N4037



TO-39
Metal Can Package

MEDIUM POWER AMPLIFIER AND SWITCHING APPLICATIONS.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	$V_{CEO(sus)}$ *	40	V
Collector Base Voltage	V_{CBO}	60	V
Emitter Base Voltage	V_{EBO}	7.0	V
Collector Current Continuous	I_C	1.0	A
Base Current	I_B	0.5	A
Continuous Power Dissipation @ or Below Ta=25°C	P_D	1.0	W
Linear Derating Dissipation		5.72	mW/°C
Operating And Storage Junction Temperature Range	T_j, T_{stg}	-65 to +200	°C

* Must not be tested on a curve tracer.

ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE	UNITS
Collector Emitter sustaining Voltage	$V_{(BR)CEO(sus)}$	$I_C=100mA, I_B=0$	>40	V
Collector Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	>60	V
Collector Cut off Current	I_{CBO}	$V_{CB}=60V, I_E=0$	<250	nA
Emitter Cut off Current	I_{EBO}	$V_{BE}=5V, I_C=0$	<20	nA
DC Current Gain	h_{FE}	$I_C=1mA, V_{CE}=10V$ $I_C=150mA, V_{CE}=10V$	>15 50-250	
Collector Emitter (sat) Voltage	$V_{CE(sat)}$	$I_C=150mA, I_B=15mA$	<1.4	V
Base Emitter Voltage	$V_{BE(on)}$	$I_C=150mA, V_{CE}=10V$	<1.5	V

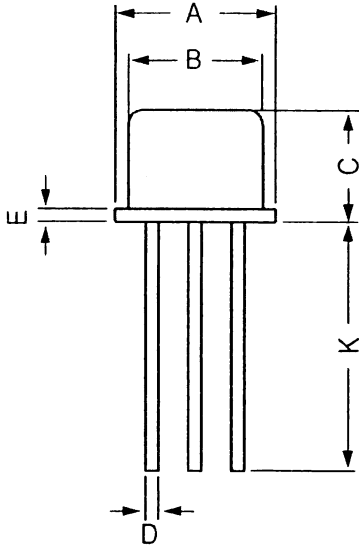
DYNAMIC CHARACTERISTICS

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE	UNITS
Collector Base Capacitance	C_{cb}	$V_{CB}=10V, f=20MHz$	<30	pF
Current Gain -High Frequency	$ h_{fe} $	$I_C=50mA, V_{CE}=10V,$ $f=20MHz$	3.0-1.0	

2N4037

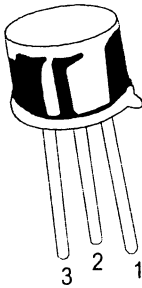
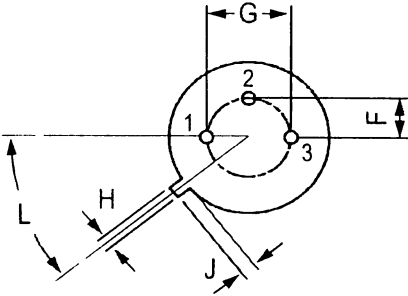
TO-39
Metal Can Package

TO-39 Metal Can Package



All dimensions are in mm

DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG



PIN CONFIGURATION
1. EMITTER
2. BASE
3. COLLECTOR